CERTIFICATE OF MAILING VIA FIRST CLASS MAIL

PURSUANT TO 37 C.F.R. '1.8, I HEREBY CERTIFY THAT I HAVE INFORMATION AND A REASONABLE BASIS FOR BELIEF THAT THIS CORRESPONDENCE WILL BE DEPOSITED AS FIRST CLASS MAIL WITH THE UNITED STATES POSTAL SERVICE IN AN ENVELOPE ADDRESSED TO:

MAIL STOP PATENT APPLICATION

ADDRESSED TO: MAIL STOP PATENT APPLI COMMISSIONER FOR PATENTS

P.O. BOX 1450

ALEXANDRIA, VA 22313-1450

Deline aller

OCTOBER 31, 2003

DATE

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Ted Johansson

Serial No.:

Filing Date: October 31, 2003

Title: Semiconductor Process and Integrated
Circuit

Serial No.:

Circuit

Group Art Unit:

Examiner:

Attny. Docket No. 068758.0139

Client Ref.: 01003US/RF/SM

INFORMATION DISCLOSURE STATEMENT

Sir:

Applicants respectfully request, pursuant to 37 C.F.R. §§1.56, 1.97 and 1.98, that the art listed on the attached PTO-1449 form be considered and cited in the examination of the above-identified application. A copy of the cited art is enclosed for the convenience of the Examiner.

Furthermore, pursuant to 37 C.F.R. §§1.97(g) and (h), no representation is made that these references are material to the patentability of the present application.

As the Information Disclosure Statement is being submitted before the mailing of the first office action on the merits, Applicants believe that no fee is required. If a fee is Date: October 31, 2003

required, please accept this transmittal as a petition therefor and charge any fee to Baker Botts L.L.P. (formerly, Baker & Botts, L.L.P.) Deposit Account No. 02-0383, Order No. (968758.0139) for any other charges necessary for the filing of this Information Disclosure Statement.

BAKER BOTTS L.L.P. (023640)

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ATTORNEYS FOR APPLICANTS

Client Reference No. 068758.0139			39	Application No.	Applicant(s): TED JOHANSSON Group Art Unit Filing Date			le .	
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